

# AGD8252B1 / AGD8252B2

High Voltage Half-Bridge Gate Driver IC

#### **General Description**

The AGD8252B1 / AGD8252B2 are 600V half-bridge gate driver ICs to control IGBTs and power MOStransistors in full-bridge and 3-phase inverter systems. Due to specially designed common mode filter, it has an excellent ruggedness on transient voltage variation.



SOP-8L (Body: 5.0 x 4.0 x 1.5 mm)

#### Features

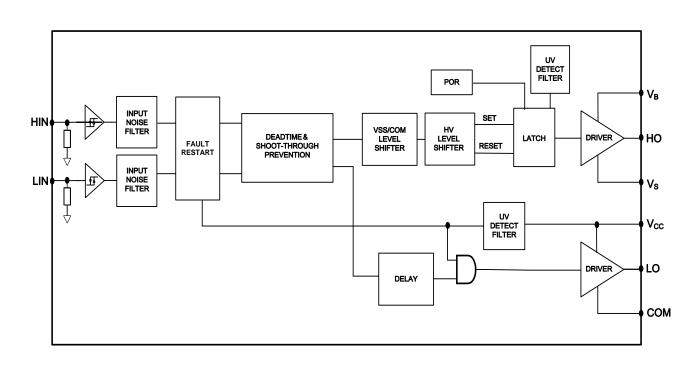
- Maximum blocking voltage +600V
- Output current: +200mA / -350mA (Typ.)
- · Matched propagation delay for both channels
- Shoot-through (cross-conduction) protection
- Under-voltage lockout protection (UVLO)
- 3.3V / 5V CMOS and TTL inputs logic compatible
- Input logic: Schmitt trigger receiver circuit (Active high)

#### Applications

- Motor drives
- Home appliances
- IGBT and power MOS gate drivers for general purpose



#### **Internal Block Diagram**

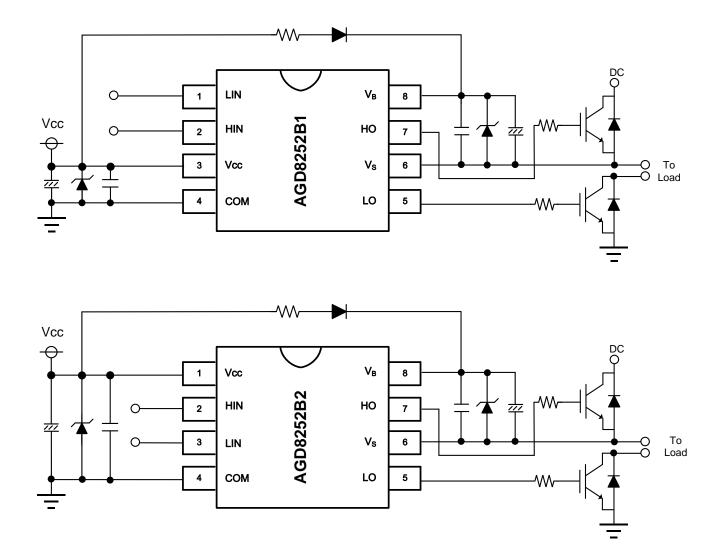




# **Ordering Information**

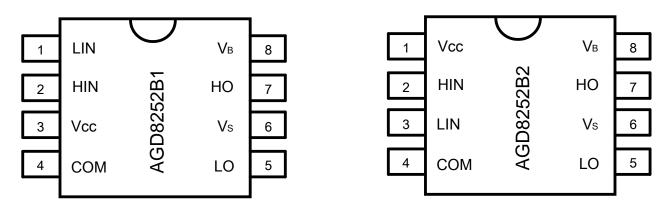
Part Number	Temperature Range	Package
AGD8252B1	-40°C to 125°C	SOP-8L
AGD8252B2	-40°C to 125°C	SOP-8L

## **Typical Application Circuit**





## **Pin Configuration**



## **Pin Description**

Pin Name	Pin Function	
V <sub>CC</sub>	Low-Side Supply Voltage	
HIN	High-Side Logic Input	
LIN	Low-Side Logic Input	
COM	Power Ground	
LO	Low-Side Driver Output	
Vs	High-Side Floating Supply Offset Voltage	
НО	High-Side Driver Output	
V <sub>B</sub>	High-Side Floating Supply Voltage	

#### **Absolute Maximum Ratings**

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute values referenced to  $V_{SS}$ , unless otherwise stated in the table.

Symbol	Parameter	Min.	Max.	Units
V <sub>CC</sub>	Low-Side Supply Voltage	-0.3	20 (1)	
V <sub>IN</sub>	Logic Input Voltage (LIN, HIN)	V <sub>SS</sub> -0.3	V <sub>CC</sub> +0.3	
VB	High-Side Floating Supply Voltage	-0.3	620	
Vs	High-Side Floating Supply Offset Voltage	V <sub>B</sub> -20 <sup>(1)</sup>	V <sub>B</sub> +0.3	V
V <sub>HO</sub>	High-Side Driver Output Voltage	V <sub>S</sub> -0.3	V <sub>B</sub> +0.3	
V <sub>LO</sub>	Low-Side Driver Output Voltage	COM-0.3	V <sub>CC</sub> +0.3	
COM	Power Ground	V <sub>CC</sub> -25	V <sub>CC</sub> +0.3	
dV <sub>S</sub> /dt	Vs Offset Voltage Slew Rate (2)	-	50	V/ns
PW <sub>HIN</sub>	High-Side Input Pulse Width	500 -		ns
PD	Package Power Dissipation @ T <sub>A</sub> ≤25°C	- 0.75		W
R <sub>thJA</sub>	Thermal Resistance, Junction to Ambient	-	- 150	
TJ	Junction Temperature	Junction Temperature - 150		
Ts	Storage Temperature	-55	150	°C
TL	Solder Reflow Condition (10 seconds)	-	300	
ESD	Human Body Model	2		kV

#### Notes:

1. An internal 20V zener diode is integrated to clamp each supply voltage.

2. Not subject of production test, verified by characterization.



### **Recommended Operating Ratings**

The device is not guaranteed to operate beyond the Recommended Operating Conditions. All voltage parameters are absolute voltages referenced to  $V_{SS}$ , unless otherwise specified. The offset rating is tested with supplies of ( $V_{CC}$ -COM) = ( $V_B$ - $V_S$ ) = 15V.

Symbol	Parameter	Min.	Max.	Units
V <sub>CC</sub>	Low-Side Supply Voltage	13.2	20	
V <sub>IN</sub>	Logic Input Voltage (LIN, HIN)	Vss	V <sub>SS</sub> +5	
VB	High-Side Floating Supply Voltage	V <sub>S</sub> +13.2	V <sub>S</sub> +20	
Vs	High-Side Floating Supply Offset Voltage <sup>(3)</sup>	COM-6	600	Ň
V <sub>S</sub> (t)	Transient High-Side Floating Supply Voltage (4)	-50	600	V
V <sub>HO</sub>	High-Side Driver Output Voltage		VB	
V <sub>LO</sub>	Low-Side Driver Output Voltage	COM	V <sub>CC</sub>	
COM	Power Ground	-5	5	
T <sub>A</sub>	Ambient Temperature	-40	125	°C

Notes:

3. Logic operation for V\_S of -6V to 600V. Logic state held for V\_S of -6V to -V\_BS.

4. Operational for transient negative  $V_S$  of  $V_{SS}$ -50V with a 50ns pulse width, which is guaranteed by design.

#### **Static Electrical Characteristics**

 $V_{CC} = V_{BS} = 15V$ .  $T_A = 25^{\circ}C$ , unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
UV <sub>CC+</sub>	V <sub>CC</sub> Under-Voltage Positive Going Threshold		10.8	11.9	13.0	
UV <sub>CC-</sub>	V <sub>CC</sub> Under-Voltage Negative Going Threshold		10.3	11.4	12.5	
UV <sub>CChys</sub>	V <sub>CC</sub> Under-Voltage Hysteresis		-	0.5	-	
$UV_{BS+}$	V <sub>BS</sub> Under-Voltage Positive Going Threshold		10.0	11.0	12.0	
UV <sub>BS-</sub>	V <sub>BS</sub> Under-Voltage Negative Going Threshold		9.0	10.0	11.0	
$UV_{BShys}$	V <sub>BS</sub> Under-Voltage Hysteresis		-	1.0	-	
I <sub>LK</sub>	High-Side Floating Supply Leakage Current	V <sub>B</sub> =V <sub>S</sub> =600V	-	-	50	μA
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> Supply Current	V <sub>IN</sub> =0V	-	70	120	μA
lacc	Quiescent V <sub>CC</sub> Supply Current	(all inputs are in the off state)	-	0.3	1	mA
V <sub>OH</sub>	High Level Output Voltage Drop, V <sub>BIAS</sub> -V <sub>O</sub>	I <sub>O</sub> =20mA, V <sub>IN</sub> =5V	-	0.9	1.4	v
V <sub>OL</sub>	Low Level Output Voltage Drop, Vo	I <sub>O</sub> =20mA, V <sub>IN</sub> =0V	-	0.4	0.6	V
I <sub>O+</sub>	Output High Short Circuit Pulsed Current	V <sub>O</sub> =0V, V <sub>IN</sub> =5V, PW≤10µs	120	200	-	
Io-	Output Low Short Circuit Pulsed Current	V <sub>O</sub> =15V, V <sub>IN</sub> =0V, PW≤10µs	250	350	-	mA
V <sub>IH</sub>	High Level Input Voltage		2.5	-	-	
V <sub>IL</sub>	Low Level Input Voltage		-	-	0.8	V
I <sub>HIN+</sub>	Input Bias Current	V <sub>HIN</sub> =5V	-	650	850	
I <sub>HIN-</sub>	Input Bias Current	V <sub>HIN</sub> =0V	-	-	1	
I <sub>LIN+</sub>	Input Bias Current	V <sub>LIN</sub> =5V	-	650	850	μA
I <sub>LIN-</sub>	Input Bias Current	V <sub>LIN</sub> =0V	-	-	1	



#### **Dynamic Electrical Characteristics**

 $V_{CC} = V_{BS} = 15V$ ,  $C_L = 1000pF$  and  $T_A = 25^{\circ}C$  unless otherwise specified.

Symbol	Definition	Conditions	Min.	Тур.	Max.	Units
t <sub>ON</sub>	Turn-On Propagation Delay		400	530	750	
t <sub>OFF</sub>	Turn-Off Propagation Delay	V <sub>IN</sub> =0V or 5V		530	750	
t <sub>R</sub>	Turn-On Rise Time			125	190	
t <sub>F</sub>	Turn-Off Fall Time			50	75	
t <sub>IN,FLT</sub>	Input Filter Time (LIN, HIN) <sup>(5)</sup>		200	350	510	ns
DT	Dead Time <sup>(6)</sup> V <sub>IN</sub> =0V or 5V without External Dead Time		190	275	420	
MT	Matching Delay Time (t <sub>ON</sub> , t <sub>OFF</sub> )	t <sub>ON(HO)</sub> - t <sub>ON(LO)</sub>   or  t <sub>OFF(HO)</sub> - t <sub>OFF(LO)</sub>	-	-	50	
PM	Output Pulse Width Matching (7)	Input Pulse Width=10µs		-	75	

Notes:

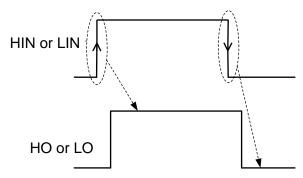
5. The minimum width of the input pulse is recommended to exceed 500ns to ensure the filtering time of the input filter is exceeded.

6. Please refer to 'Dead Time' definition of 'Function Diagram'.

7. PM is defined as |(Input Pulse Width) – (Output Pulse Width)|.



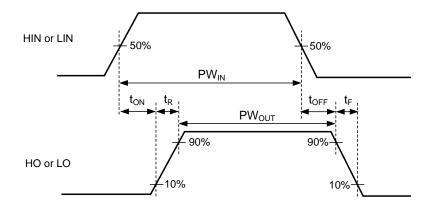
## **Output Activation**



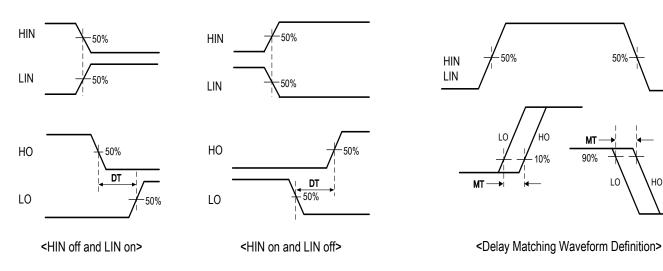
HIN	N LIN HO		LO
Н	L	н	L
L	Н	L	Н

Note: Output signal (HO or LO) is triggered by the edge of input signal.

## Input / Output Timing Diagram



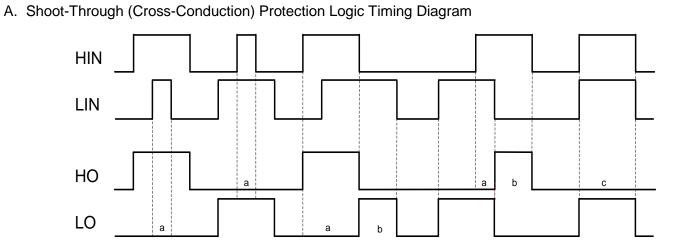
## **Dead Time Activation**



HO



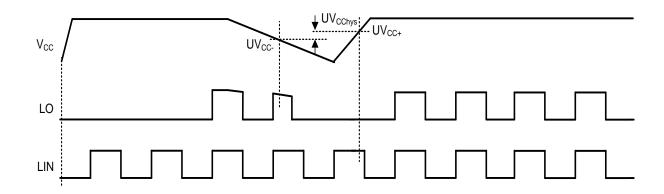
#### **Function Timing Diagram**



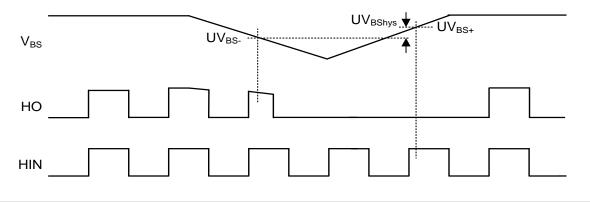
#### Notes:

- a. When one output (high or low side) is turned on, the other side turn-on input is ignored.
- b. If both outputs are changed simultaneously, the turn-on activation is done by the internal dead time of 275ns typ. (For more information, please refer to below 'Dead Time' section.)
- c. When high-side (HIN) and low-side (LIN) have turn-on inputs at the same time, low-side (LIN) has the priority.

#### B. V<sub>CC</sub> Supply Under-Voltage (UV) Lockout Timing Diagram

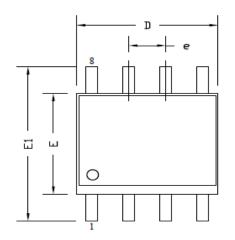


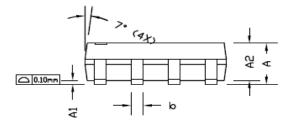
C. V<sub>BS</sub> Supply Under-Voltage (UV) Lockout Timing Diagram

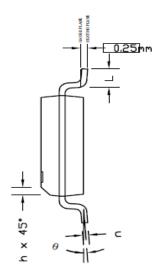




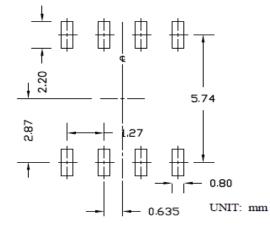
#### Package Dimensions, SOP-8L







#### RECOMMENDED LAND PATTERN



SYMBOLS	DIMENSIO	NS IN MILL	IMETERS	DIME	ISIONS IN IN	ICHES
SIMBOLS	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.35	1.65	1.75	0.053	0.065	0.069
A1	0.10	0.15	0.25	0.004	0.006	0.010
A2	1.25	1.50	1.65	0.049	0.059	0.065
b	0.31	0.41	0.51	0.012	0.016	0.020
с	0.17	0.20	0.25	0.007	0.008	0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
E	3.80	3.90	4.00	0.150	0.154	0.157
e	1.27 BSC			0	.050 BSC	
E1	5.80	6.00	6.20	0.228	0.236	0.244
h	0.25	0.30	0.50	0.010	0.012	0.020
L	0.40	0.69	1.27	0.016	0.027	0.050
θ	<b>0</b> °	4°	<b>8</b> °	<b>0</b> °	4°	8°

NOTE

- 1. ALL DIMENSIONS ARE IN MILLMETERS.
- 2. DIMENSIONS ARE INCLUSIVE OF PLATING.
- 3. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
- 4. DIMENSION L IS MEASURED IN GAUGE PLANE.
- 5. CONTROLLING DIMENSION IS MILLIMETER.
- CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.



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